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(54) **LIGHT-EMITTING DEVICE, DISPLAY APPARATUS INCLUDING THE SAME AND METHOD FOR MANUFACTURING THE DEVICE AND APPARATUS**

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ABSTRACT

A light-emitting device, display apparatus including the same and method for manufacturing the device and apparatus are disclosed. The light-emitting device includes a nitride semiconductor structure including a first semiconductor layer, an active layer and a second semiconductor layer; a passivation pattern disposed on an outer surface of the nitride semiconductor structure; a first electrode connected to the first semiconductor layer; and a second electrode spaced apart from the first electrode and connected to the second semiconductor layer, wherein each of the first electrode and the second electrode includes a silicide alloy. Accordingly, the defect in manufacturing the electrode of the light-emitting device due to the bowing phenomenon of the growth substrate may be removed.

